

Konstantin Kotlyar

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/2540506/publications.pdf>

Version: 2024-02-01

39
papers

118
citations

1478505

6
h-index

1372567

10
g-index

39
all docs

39
docs citations

39
times ranked

124
citing authors

#	ARTICLE	IF	CITATIONS
1	Polymer-salt synthesis and characterization of MgO-ZnO ceramic coatings with the high transparency in UV spectral range. <i>Optical Materials</i> , 2018, 82, 81-87.	3.6	22
2	Growth and optical properties of filamentary GaN nanocrystals grown on a hybrid SiC/Si(111) substrate by molecular beam epitaxy. <i>Physics of the Solid State</i> , 2016, 58, 1952-1955.	0.6	10
3	Thermal Penetration of Gold Nanoparticles into Silicon Dioxide. <i>Acta Physica Polonica A</i> , 2017, 132, 366-369.	0.5	10
4	Room temperature lasing from microdisk laser in aqueous medium. <i>Journal of Physics: Conference Series</i> , 2018, 1124, 051007.	0.4	8
5	Low temperature plasma enhanced deposition approach for fabrication of microcrystalline GaP/Si superlattice. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 2018, 36, 02D408.	2.1	7
6	Oxygen Nitrogen Mixture Effect on Aluminum Nitride Synthesis by Reactive Ion Plasma Deposition. <i>Semiconductors</i> , 2018, 52, 184-188.	0.5	7
7	Study of SiC buffer layer thickness influence on photovoltaic properties of n-GaN NWs/SiC/p-Si heterostructure. <i>Materials Science in Semiconductor Processing</i> , 2019, 90, 20-25.	4.0	7
8	MBE growth and optical properties of GaN nanowires on SiC/Si(111) hybrid substrate. <i>AIP Conference Proceedings</i> , 2016, , .	0.4	6
9	New method for MBE growth of GaAs nanowires on silicon using colloidal Au nanoparticles. <i>Nanotechnology</i> , 2018, 29, 045602.	2.6	6
10	Solar Cell Based on Core/Shell Nanowires. <i>Semiconductors</i> , 2018, 52, 1568-1572.	0.5	4
11	The use of SiC/Si(111) hybrid substrate for MBE growth of GaN nanowires. <i>Journal of Physics: Conference Series</i> , 2016, 741, 012027.	0.4	3
12	Structural and Optical Properties of Wurtzite AlGaAs Nanowires Grown by MBE on Si(111) Substrate. <i>Semiconductors</i> , 2018, 52, 2146-2148.	0.5	3
13	Processing of GaN/Si(111) Epitaxial Structures for MEMS Applications. <i>Semiconductors</i> , 2018, 52, 2117-2119.	0.5	3
14	Study of p-type contact topography influence on characteristics of microdisk and microring lasers. <i>Journal of Physics: Conference Series</i> , 2018, 1124, 041012.	0.4	3
15	Fabrication of the structures with autocatalytic CdTe nanowires using magnetron sputtering deposition. <i>Physics of the Solid State</i> , 2016, 58, 2401-2405.	0.6	2
16	MBE growth of GaAs and InAs nanowires using colloidal Ag nanoparticles. <i>Journal of Physics: Conference Series</i> , 2017, 917, 032035.	0.4	2
17	MBE growth and Structural Properties of InAs and InGaAs Nanowires with Different Mole Fraction of In on Si and Strongly Mismatched SiC/Si(111) Substrates. <i>Semiconductors</i> , 2018, 52, 651-653.	0.5	2
18	MBE Growth and Structural Properties of GaP and InP Nanowires on a SiC Substrate with a Graphene Layer. <i>Semiconductors</i> , 2018, 52, 1428-1431.	0.5	2

#	ARTICLE	IF	CITATIONS
19	Phosphorus-Based Nanowires Grown by Molecular-Beam Epitaxy on Silicon. <i>Semiconductors</i> , 2018, 52, 1416-1419.	0.5	2
20	Development of methods for orderly growth of nanowires. <i>Journal of Physics: Conference Series</i> , 2015, 661, 012053.	0.4	1
21	InGaN/GaN heterostructures with lateral confinement for light emitting diodes. <i>Journal of Physics: Conference Series</i> , 2016, 741, 012083.	0.4	1
22	Optical field distribution in quasy-ID nanostructures. <i>Journal of Physics: Conference Series</i> , 2016, 741, 012154.	0.4	1
23	MBE growth of ultrathin III-V nanowires on a highly mismatched SiC/Si(111) substrate. <i>Semiconductors</i> , 2017, 51, 1472-1476.	0.5	1
24	Influence of dry etching condition to geometry of vertically aligned silicon nanostructures. <i>Journal of Physics: Conference Series</i> , 2017, 917, 052030.	0.4	1
25	Injection microdisk lasers based on multilayers of InGaAs/GaAs quantum well-dot structures. <i>Journal of Physics: Conference Series</i> , 2018, 1124, 041002.	0.4	1
26	Temperature annealing effect on ITO film. <i>Journal of Physics: Conference Series</i> , 2018, 1124, 041035.	0.4	1
27	MBE growth of GaAs nanowires with modulated crystal structure. <i>Journal of Physics: Conference Series</i> , 2018, 1124, 022043.	0.4	1
28	InGaN/GaN QDs nanorods for light emitters: Processing and properties. <i>AIP Conference Proceedings</i> , 2019, , .	0.4	1
29	MBE growth and optical properties of GaN nanowires on SiC/Si(111) hybrid substrate. , 2016, , .		0
30	Features of AlN film grown by ion-plasma sputtering. <i>Journal of Physics: Conference Series</i> , 2016, 741, 012041.	0.4	0
31	MBE growth and optical properties of GaN layers on SiC/Si(111) hybrid substrate. <i>Journal of Physics: Conference Series</i> , 2017, 917, 032014.	0.4	0
32	The Features of GaAs Nanowire SEM Images. <i>Semiconductors</i> , 2018, 52, 605-608.	0.5	0
33	InGaN/GaN QDs Nanorods: Processing and Properties. <i>Semiconductors</i> , 2018, 52, 2096-2098.	0.5	0
34	Effect of temperature on dry etching of III-V structures. <i>Journal of Physics: Conference Series</i> , 2018, 1124, 041031.	0.4	0
35	Influence of coating layers on characteristics of microdisk lasers with InAs/InGaAs quantum dots active region. <i>Journal of Physics: Conference Series</i> , 2018, 1124, 041020.	0.4	0
36	MBE Growth and Optical Properties of GaN, InN, and A3 B5 Nanowires on SiC/Si(111) Hybrid Substrate. <i>Advances in Condensed Matter Physics</i> , 2018, 2018, 1-5.	1.1	0

#	ARTICLE	IF	CITATIONS
37	MBE Growth and Optical Properties of III-V Nanowires on SiC/Si(111) Hybrid Substrate. , 2018, , .		0
38	Optical properties of Al _x Ga _{1-x} As nanowires with different composition in Al. AIP Conference Proceedings, 2019, , .	0.4	0
39	Influence of cryogenic dry etching on minority carriers lifetime in vertically aligned silicon nanostructures. AIP Conference Proceedings, 2019, , .	0.4	0